

INK0003AX SERIES

High speed switching
Silicon N-channel MOSFET

DESCRIPTION

INK0003AX is a Silicon N-channel MOSFET. This product is most suitable for low voltage use such as portable machinery, because of low voltage drive and low on resistance.

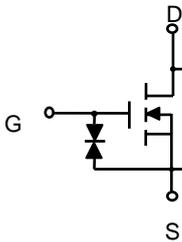
FEATURE

- Input impedance is high, and not necessary to consider a drive electric current.
- Drive voltage 2.5V
- Low on Resistance.
 $R_{DS(ON)}=0.9\Omega$ (TYP) @ $I_D=100\text{mA}$, $V_{GS}=4.0\text{V}$
- High speed switching.
- Small package for easy mounting.

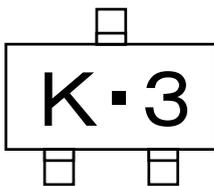
APPLICATION

High speed switching, Analog switching

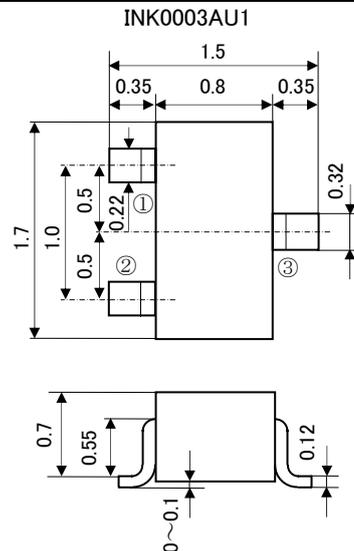
EQUIVALENT CIRCUIT



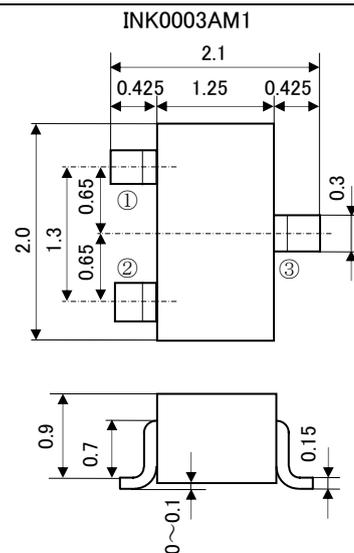
MARKING



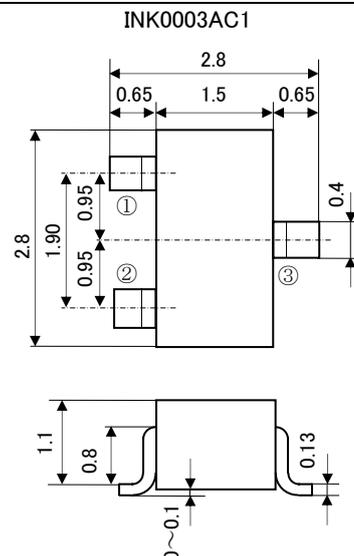
OUTLINE DRAWING (Unit:mm)



JEITA: SC-75A
JEDEC: —
TERMINAL CONNECTOR
①: GATE
②: SOURCE
③: DRAIN



JEITA: SC-70
JEDEC: —
TERMINAL CONNECTOR
①: GATE
②: SOURCE
③: DRAIN



JEITA: SC-59
JEDEC: Similar to TO-236
TERMINAL CONNECTOR
①: GATE
②: SOURCE
③: DRAIN

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MAXIMUM RATING (Ta=25°C)

SYMBOL	PARAMETER	RATING			UNIT
		INK0003AU1	INK0003AM1	INK0003AC1	
V _{DSS}	Drain-source voltage	20			V
V _{GSS}	Gate-source voltage	±8			V
I _D	Drain current(DC)	200			mA
I _{DP}	Drain current(Pulse)	400(※1)			mA
P _D	Total power dissipation	150	200		mW
T _{ch}	Channel temperature	+150			°C
T _{stg}	Range of Storage temperature	-55~+150			°C

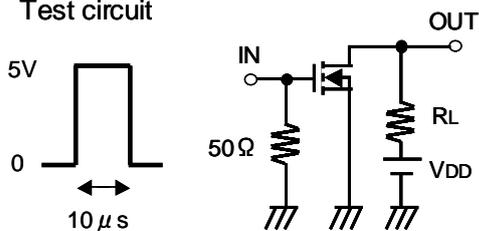
※1: P_w ≤ 10μs, Duty cycle ≤ 1%

ELECTRICAL CHARACTERISTICS (Ta=25°C)

SYMBOL	PARAMETER	TEST CONDITION	LIMIT			UNIT
			MIN	TYP	MAX	
V _{(BR)DSS}	Drain-source breakdown voltage	I _D =100μA, V _{Gs} =0V	20	-	-	V
I _{GSS}	Gate-source leak current	V _{Gs} =±5V, V _{Ds} =0V	-	-	±0.5	μA
I _{DSS}	Zero gate voltage drain current	V _{Ds} =20V, V _{Gs} =0V	-	-	1.0	μA
V _{th}	Gate threshold voltage	I _D =250μA, V _{Ds} =V _{Gs}	0.6	-	1.2	V
Y _{fs}	Forward transfer admittance	V _{Ds} =10V, I _D =0.1A	-	300	-	mS
R _{DS(ON)}	Static drain-source on-state resistance	I _D =100mA, V _{Gs} =4.0V	-	0.9	-	Ω
C _{iss}	Input capacitance	V _{Ds} =10V, V _{Gs} =0V, f=1MHz	-	34	-	pF
C _{oss}	Output capacitance		-	8.5	-	
t _{on}	Switching time	V _{DD} =5V, I _D =10mA	-	14	-	ns
t _{off}		V _{Gs} =0~5V	-	85	-	

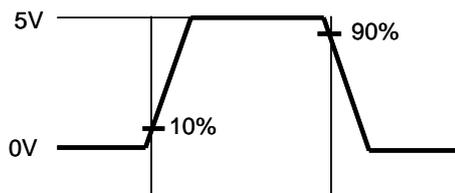
Switching time test condition

Test circuit

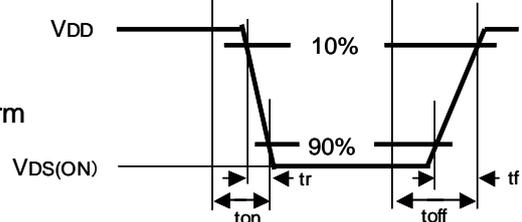


V_{DD}=5V
Duty ≤ 1%
Common source
Ta=25°C

Input Waveform



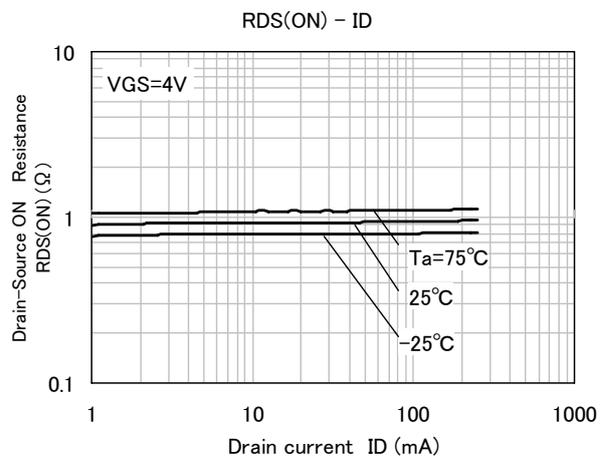
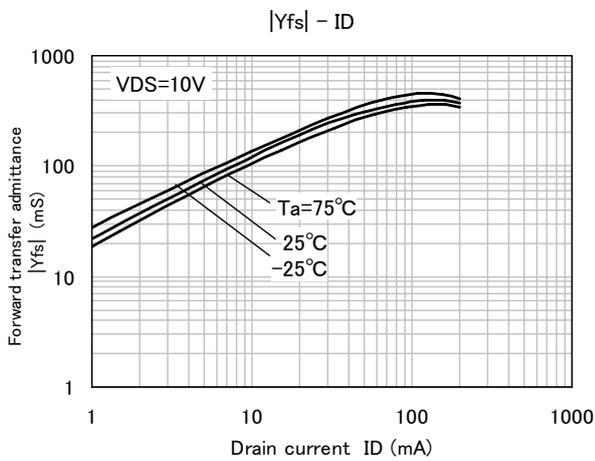
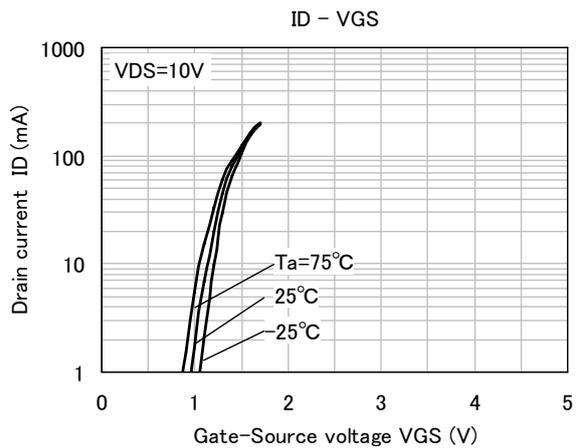
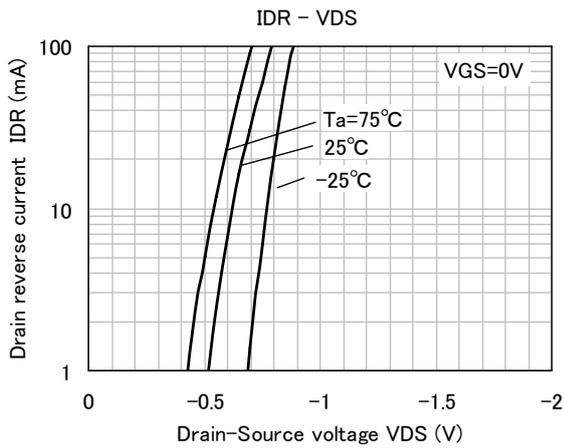
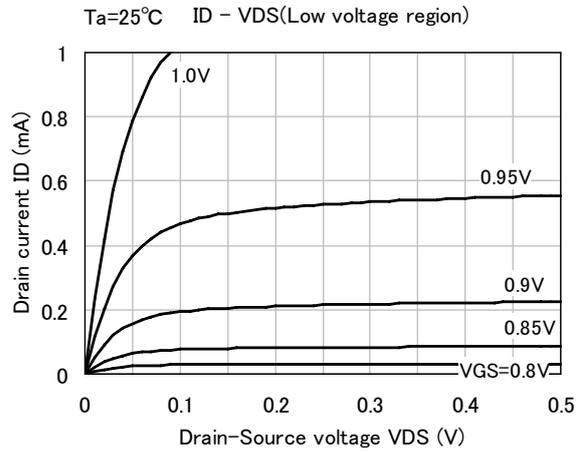
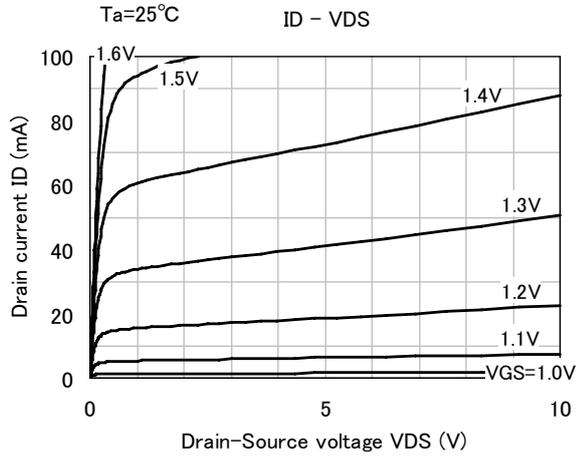
Output Waveform



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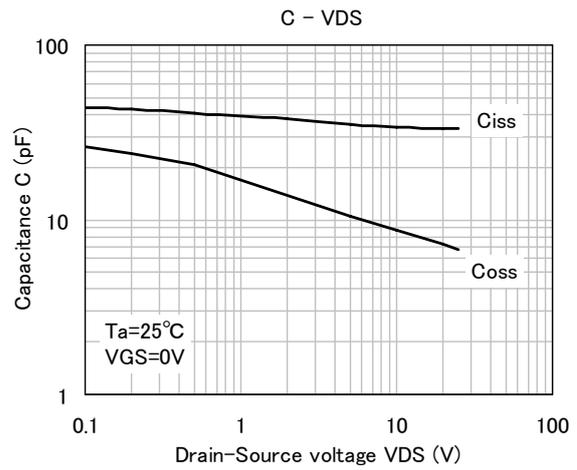
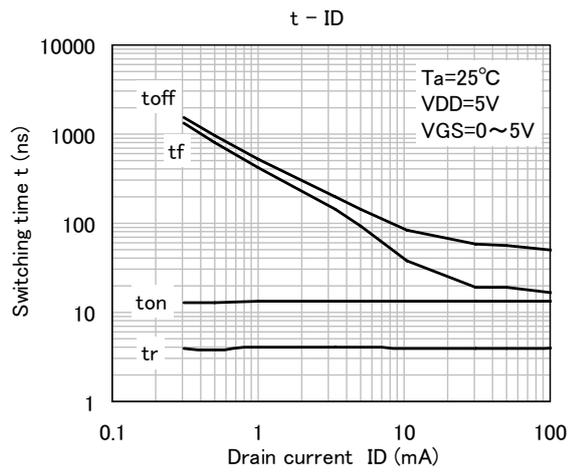
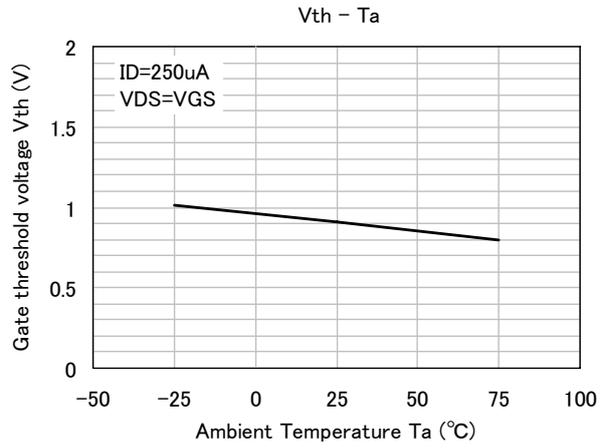
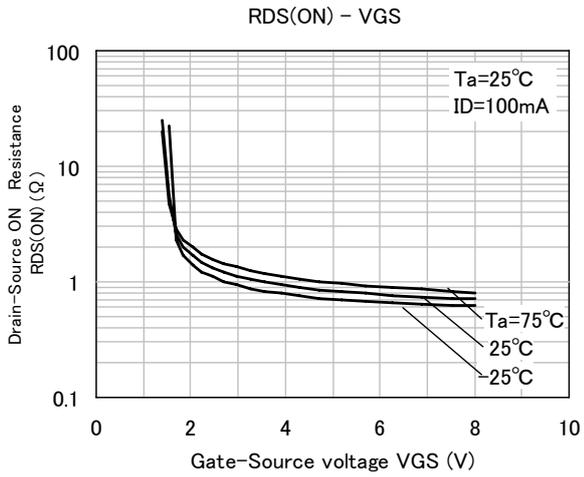
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TYPICAL CHARACTERISTICS



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Keep safety first in your circuit designs!

·ISAHAYA Electronics Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (1) placement of substitutive, auxiliary, (2) use of non-flammable material or (3) prevention against any malfunction or mishap.

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